



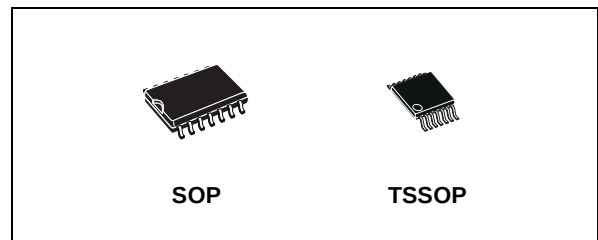
74LVX126

LOW VOLTAGE CMOS QUAD BUS BUFFERS (3-STATE) WITH 5V TOLERANT INPUTS

- HIGH SPEED:
 $t_{PD}=4.4ns$ (TYP.) at $V_{CC} = 3.3V$
- 5V TOLERANT INPUTS
- POWER-DOWN PROTECTION ON INPUTS
- INPUT VOLTAGE LEVEL:
 $V_{IL} = 0.8V$, $V_{IH} = 2V$ at $V_{CC} = 3V$
- LOW POWER DISSIPATION:
 $I_{CC} = 2 \mu A$ (MAX.) at $T_A=25^{\circ}C$
- LOW NOISE:
 $V_{OLP} = 0.3V$ (TYP.) at $V_{CC} = 3.3V$
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 4 mA$ (MIN) at $V_{CC} = 3V$
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \approx t_{PHL}$
- OPERATING VOLTAGE RANGE:
 $V_{CC}(OPR) = 2V$ to $3.6V$ (1.2V Data Retention)
- PIN AND FUNCTION COMPATIBLE WITH
74 SERIES 126
- IMPROVED LATCH-UP IMMUNITY

DESCRIPTION

The 74LVX126 is a low voltage CMOS QUAD BUS BUFFERS fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology. It is ideal for low power, battery operated and low noise 3.3V applications.



ORDER CODES

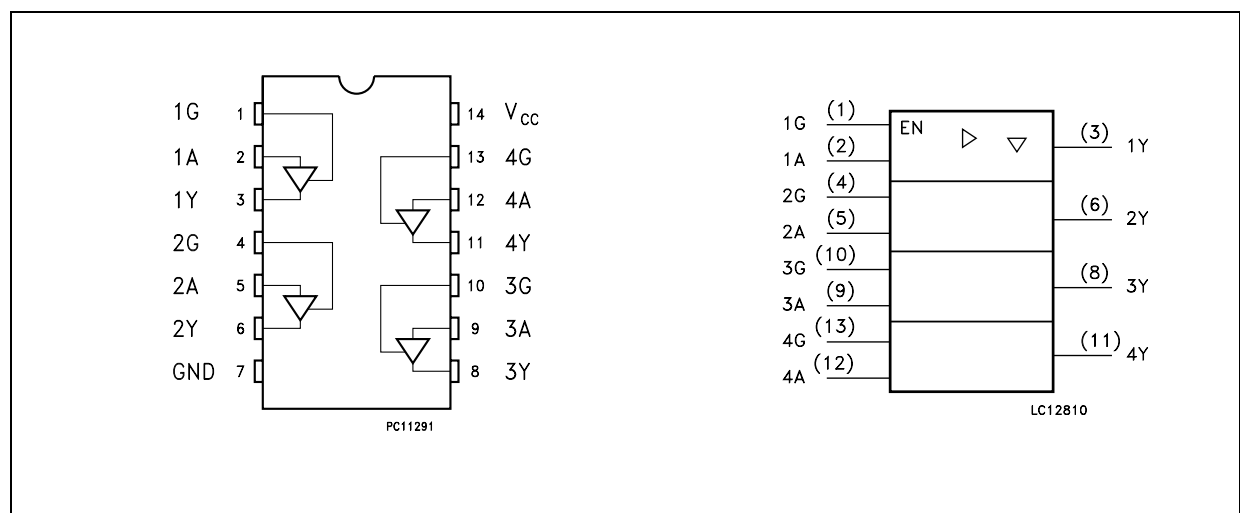
PACKAGE	TUBE	T & R
SOP	74LVX126M	74LVX126MTR
TSSOP		74LVX126TTR

This device requires the 3-STATE control input G to be set low to place the output go in to the high impedance state.

Power down protection is provided on all inputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 5V to 3V. It combines high speed performance with the true CMOS low power consumption.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



The diagram illustrates an ESD protection circuit for an input signal. The input line, labeled "INPUT", is connected to a node that branches into three parallel paths to ground (GND):

- A direct connection to ground through a component labeled "ESD PROTEC.".
- A connection to ground through a diode (represented by a triangle pointing towards ground).
- A connection to ground through a series combination of a resistor (represented by a rectangle) and another diode (also pointing towards ground).

A dashed line connects the two diodes, indicating they are part of the same protection structure. The ground connections are labeled "GND".

SC11940

PIN No	SYMBOL	NAME AND FUNCTION
1, 4, 10, 13	1G to 4G	Output Enable Inputs
2, 5, 9, 12	1A to 4A	Data Inputs
3, 6, 8, 11	1Y to 4Y	Data Outputs
7	GND	Ground (0V)
14	V _{CC}	Positive Supply Voltage

A	G	Y
X	L	Z
L	H	L
H	H	H

X : Don't Care
Z : High Impedance

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7.0	V
V_I	DC Input Voltage	-0.5 to +7.0	V
V_O	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
I_{IK}	DC Input Diode Current	- 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Current	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage (note 1)	2 to 3.6	V
V_I	Input Voltage	0 to 5.5	V
V_O	Output Voltage	0 to V_{CC}	V
T_{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 2) ($V_{CC} = 3V$)	0 to 100	ns/V

1) Truth Table guaranteed: 1.2V to 3.6V

- 1) Truth Table guarantee
- 2) V_{IN} from 0.8V to 2.0V

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _{IH}	High Level Input Voltage	2.0		1.5			1.5		1.5		V
		3.0		2			2		2		
		3.6		2.4			2.4		2.4		
V _{IL}	Low Level Input Voltage	2.0				0.5		0.5		0.5	V
		3.0				0.8		0.8		0.8	
		3.6				0.8		0.8		0.8	
V _{OH}	High Level Output Voltage	2.0	I _O =-50 μA	1.9	2.0		1.9		1.9		V
		3.0	I _O =-50 μA	2.9	3.0		2.9		2.9		
		3.0	I _O =-4 mA	2.58			2.48		2.4		
V _{OL}	Low Level Output Voltage	2.0	I _O =50 μA		0.0	0.1		0.1		0.1	V
		3.0	I _O =50 μA		0.0	0.1		0.1		0.1	
		3.0	I _O =4 mA			0.36		0.44		0.55	
I _{OZ}	High Impedance Output Leakage Current	3.6	V _I = V _{IH} or V _{IL} V _O = V _{CC} or GND			±0.25		± 2.5		± 5	μA
I _I	Input Leakage Current	3.6	V _I = 5.5V or GND			± 0.1		± 1		± 1	μA
I _{CC}	Quiescent Supply Current	3.6	V _I = V _{CC} or GND			2		20		20	μA

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _{OLP}	Dynamic Low Voltage Quiet Output (note 1, 2)	3.3	C _L = 50 pF		0.3	0.5					V
V _{OLV}				-0.5	-0.3						
V _{IHD}	Dynamic High Voltage Input (note 1, 3)	3.3		2.0							
V _{ILD}	Dynamic Low Voltage Input (note 1, 3)	3.3					0.8				

1) Worst case package.

2) Max number of outputs defined as (n). Data inputs are driven 0V to 3.3V, (n-1) outputs switching and one output at GND.

3) Max number of data inputs (n) switching. (n-1) switching 0V to 3.3V. Inputs under test switching: 3.3V to threshold (V_{ILD}), 0V to threshold (V_{IHD}), f=1MHz.

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3\text{ns}$)

Symbol	Parameter	Test Condition			Value						Unit	
		V _{CC} (V)	C _L (pF)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
					Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t _{PLH} t _{PHL}	Propagation Delay Time	2.7	15			5.8	8.0	1.0	9.6	1.0	11.5	ns
		2.7	50			7.0	10.5	1.0	12.6	1.0	15.0	
		3.3 ^(*)	15			4.4	6.2	1.0	8.5	1.0	9.5	
		3.3 ^(*)	50			5.9	9.7	1.0	12.0	1.0	13.5	
t _{PZL} t _{PZH}	Output Enable Time	2.7	15			8.9	11.5	1.0	12.5	1.0	12.5	ns
		2.7	50			10.0	14.0	1.0	16.0	1.0	16.0	
		3.3 ^(*)	15			8.0	10.4	1.0	11.5	1.0	11.5	
		3.3 ^(*)	50			8.9	12	1.0	13.0	1.0	13.0	
t _{PLZ} t _{PHZ}	Output Disable Time	2.7	50			7.2	11.0	1.0	13.0	1.0	15.6	ns
		3.3 ^(*)	50			6.0	8.5	1.0	11.0	1.0	13.0	
t _{OSLH} t _{OSHL}	Output to Output Skew Time (note 1,2)	2.7	50			0.5	1.0		1.5		1.5	ns
		3.3 ^(*)	50			0.5	1.0		1.5		1.5	

1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW

2) Parameter guaranteed by design

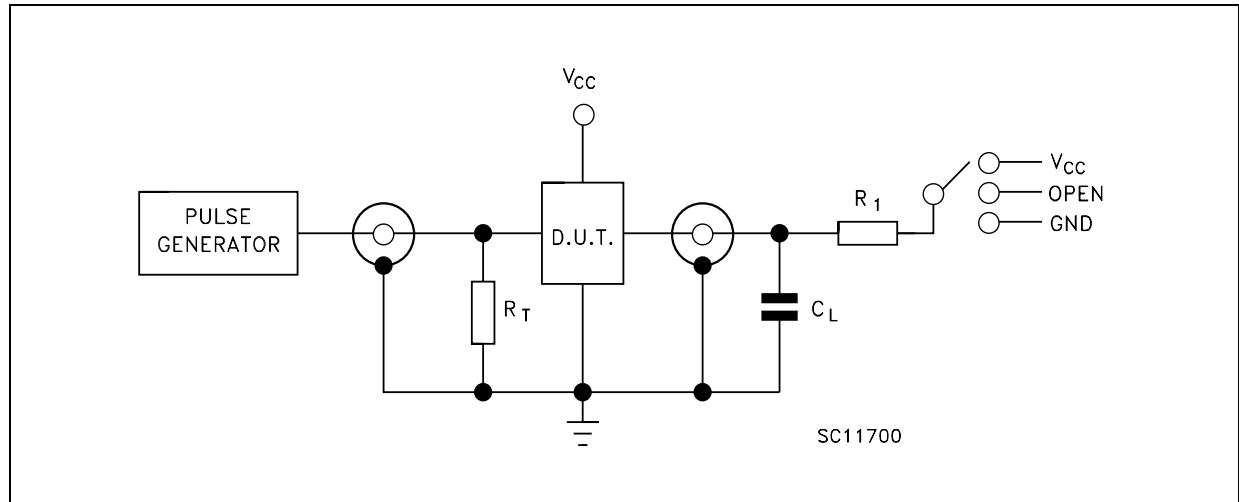
(*) Voltage range is $3.3\text{V} \pm 0.3\text{V}$

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
C _{IN}	Input Capacitance	3.3			4	10		10		10	pF
C _{OUT}	Output Capacitance	3.3			6						pF
C _{PD}	Power Dissipation Capacitance (note 1)	3.3			14						pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(OPR)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/4$ (per circuit)

TEST CIRCUIT

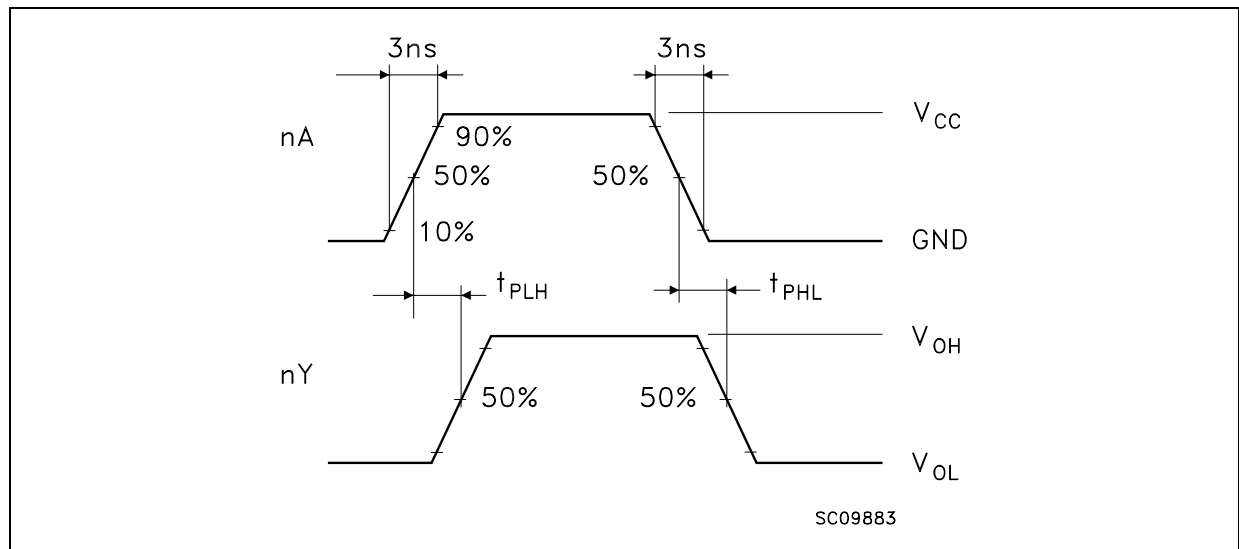


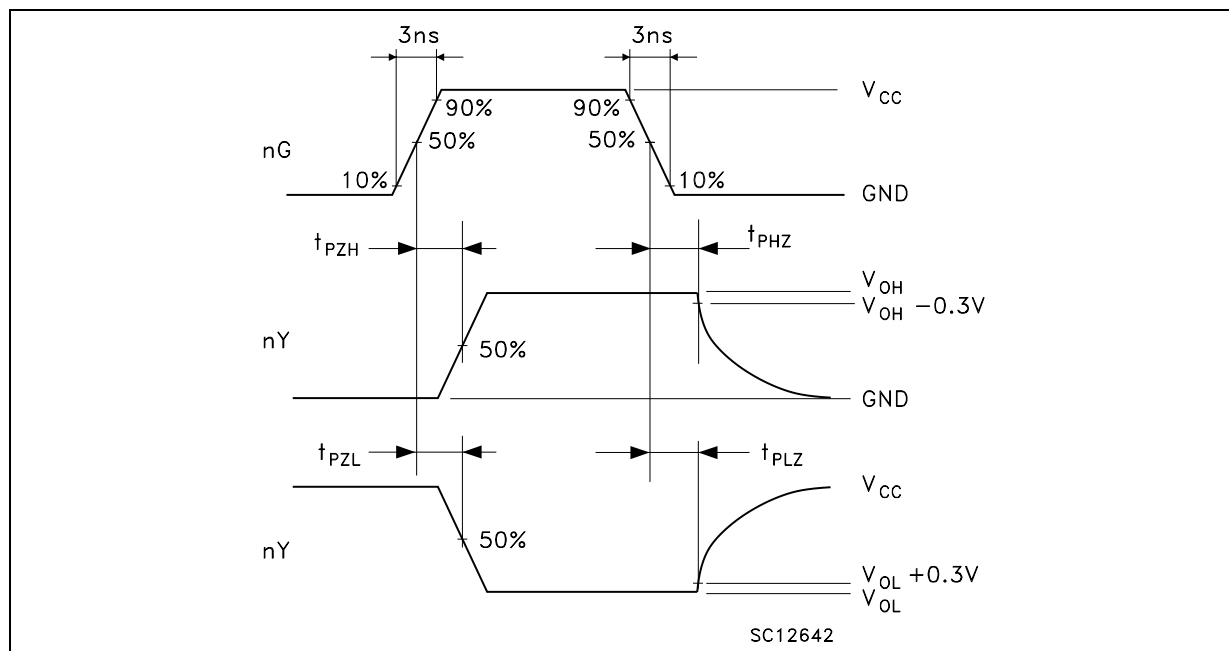
TEST	SWITCH
t_{PLH} , t_{PHL}	Open
t_{PZL} , t_{PLZ}	V_{CC}
t_{PZH} , t_{PHZ}	GND

$C_L = 15/50\text{pF}$ or equivalent (includes jig and probe capacitance)

$R_L = R_1 = 1\text{K}\Omega$ or equivalent

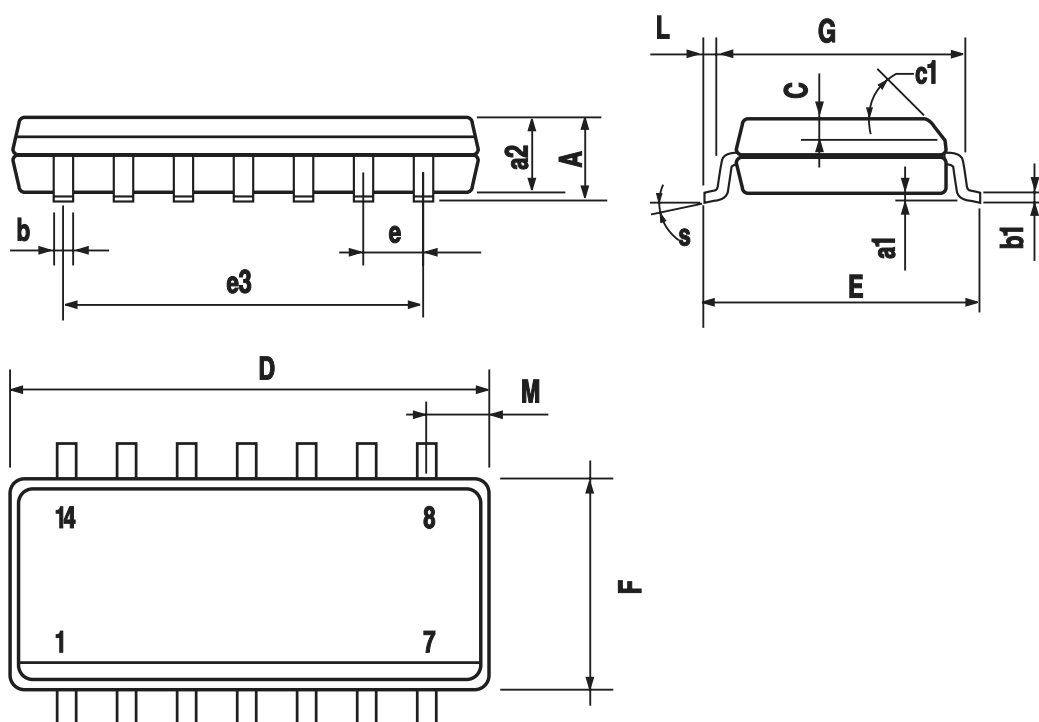
$R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

WAVEFORM 1 : PROPAGATION DELAYS ($f=1\text{MHz}$; 50% duty cycle)



SO-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



PO13G

TSSOP14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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